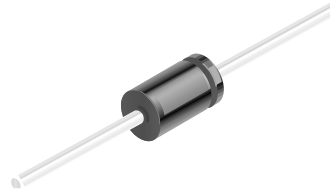


# EGP10A - EGP10K

## Features

- Superfast recovery time for high efficiency.
- Low forward voltage, high current capability.
- Low leakage current.
- High surge current capability.



**DO-41**  
COLOR BAND DENOTES CATHODE

## Fast Rectifiers (Glass Passivated)

### Absolute Maximum Ratings\* T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value								Units
		10A	10B	10C	10D	10F	10G	10J	10K	
V <sub>RRM</sub>	Maximum Repetitive Reverse Voltage	50	100	150	200	300	400	600	800	V
I <sub>F(AV)</sub>	Average Rectified Forward Current, .375 " lead length @ T <sub>L</sub> = 55°C	1.0								A
I <sub>FSM</sub>	Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave	30								A
T <sub>stg</sub>	Storage Temperature Range	-65 to +150								°C
T <sub>J</sub>	Operating Junction Temperature	-65 to +150								°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

P <sub>D</sub>	Power Dissipation	2.5								W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	50								°C/W

### Electrical Characteristics T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Device								Units
		10A	10B	10C	10D	10F	10G	10J	10K	
V <sub>F</sub>	Forward Voltage @ 1.0 A	0.95				1.25		1.7		V
t <sub>rr</sub>	Reverse Recovery Time I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1.0 A, I <sub>rr</sub> = 0.25 A	50						75		ns
I <sub>R</sub>	Reverse Current @ rated V <sub>R</sub> T <sub>A</sub> = 25°C T <sub>A</sub> = 125°C	5.0				100				μA μA
C <sub>T</sub>	Total Capacitance V <sub>R</sub> = 4.0 V, f = 1.0 MHz	22				15				pF

## Typical Characteristics

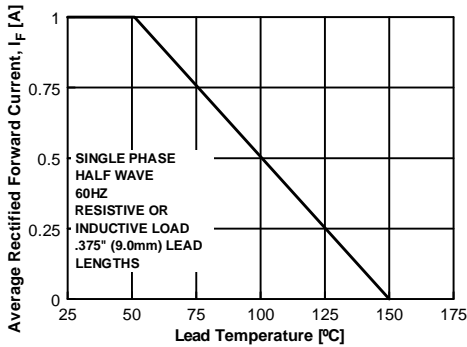


Figure 1. Forward Current Derating Curve

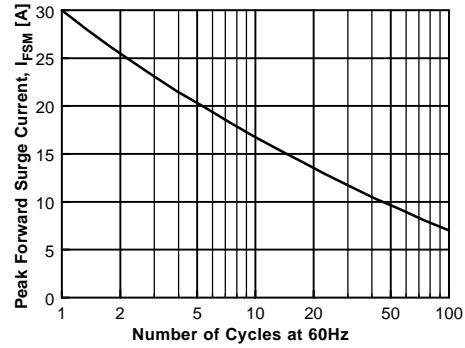


Figure 2. Non-Repetitive Surge Current

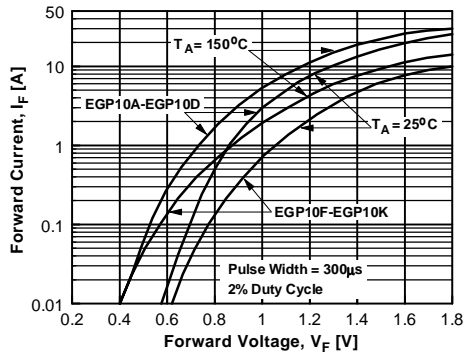


Figure 3. Forward Voltage Characteristics

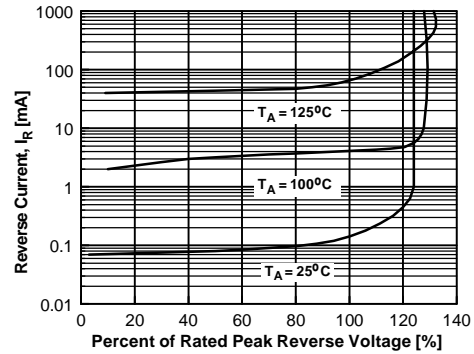


Figure 4. Reverse Current vs Reverse Voltage

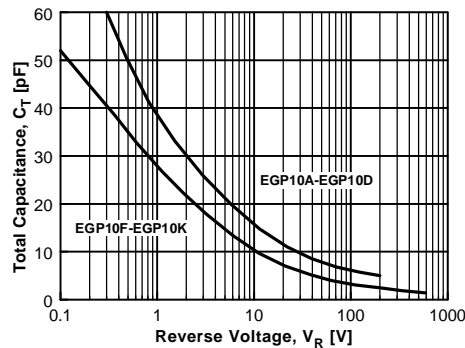
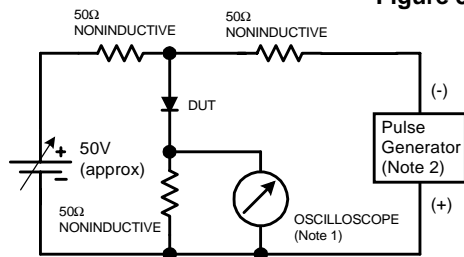
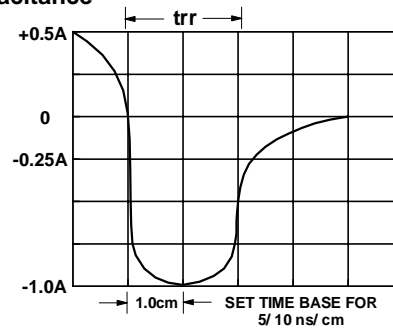


Figure 5. Total Capacitance



- NOTES:  
 1. Rise time = 7.0 ns max; Input impedance = 1.0 megaohm 22 pf.  
 2. Rise time = 10 ns max; Source impedance = 50 ohms.



Reverse Recovery Time Characteristic and Test Circuit Diagram

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